

BSR50

NPN Darlington Transistor

- This device designed for applications requiring extremely high gain at WWW.DZSC.CO collector currents to 0.5A.
- Sourced from Process 06.



1. Emitter 2. Collector 3. Base WWW.DZSC.CO

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage 5		V
Ic	Collector Current	1.5	А
T _J , T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	45			V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_B = 0$	60			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 45V, I_{E} = 0$			50	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4.0V, I_{C} = 0$			50	nA
h _{FE}	DC Current Gain	$V_{CE} = 10V, I_{C} = 150mA$ $V_{CE} = 10V, I_{C} = 0.5A$	1,000 2,000			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{A}, I_B = 4.0 \text{mA}$			1.3 1.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 500 \mu \text{A}$ $I_C = 1.0 \text{mA}, I_B = 4.0 \text{mA}$		ea-	0.9 2.2	L C V C C

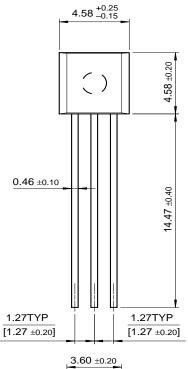
Thermal Characteristics T_A=25°C unless otherwise noted

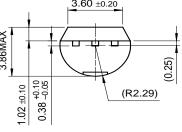
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case 83.3 °C		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient 200 °C		°C/W

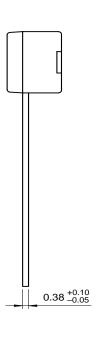


Package Dimensions

TO-92







Dimensions in Millimeters

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